

NTZD3155C

Small Signal MOSFET

Complementary 20 V, 540 mA / -430 mA,
with ESD protection, SOT-563 package.

Features

- Leading Trench Technology for Low $R_{DS(on)}$ Performance
- High Efficiency System Performance
- Low Threshold Voltage
- ESD Protected Gate
- Small Footprint 1.6 x 1.6 mm
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Conversion Circuits
- Load/Power Switching with Level Shift
- Single or Dual Cell Li-Ion Battery Operated Systems
- High Speed Circuits
- Cell Phones, MP3s, Digital Cameras, and PDAs

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	20	V
Gate-to-Source Voltage			V_{GS}	± 6	V
N-Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	540	mA
		$T_A = 85^{\circ}\text{C}$		390	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		570	
P-Channel Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$		-430	
		$T_A = 85^{\circ}\text{C}$		-310	
	$t \leq 5\text{ s}$	$T_A = 25^{\circ}\text{C}$		-455	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	250	mW
				$t \leq 5\text{ s}$	
Pulsed Drain Current	N-Channel	$t_p = 10\text{ }\mu\text{s}$	I_{DM}	1500	mA
	P-Channel			-750	
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq [1 oz] including traces).

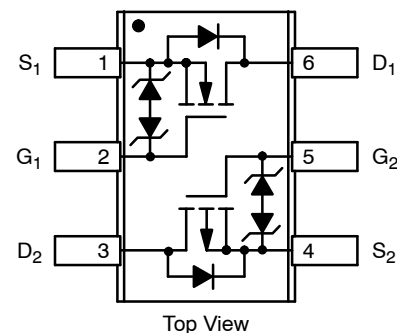


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max (Note 1)
N-Channel 20 V	0.4 Ω @ 4.5 V	540 mA
	0.5 Ω @ 2.5 V	
	0.7 Ω @ 1.8 V	
P-Channel -20 V	0.5 Ω @ -4.5 V	-430 mA
	0.6 Ω @ -2.5 V	
	1.0 Ω @ -1.8 V	

PINOUT: SOT-563



SOT-563-6
CASE 463A

MARKING DIAGRAM



TW = Specific Device Code
M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTZD3155CT1G	SOT-563 (Pb-Free)	4000 / Tape & Reel
NTZD3155CT1H		
NTZD3155CT2G	SOT-563 (Pb-Free)	4000 / Tape & Reel
NTZD3155CT2H		
NTZD3155CT5G	SOT-563 (Pb-Free)	8000 / Tape & Reel
NTZD3155CT5H		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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Thermal Resistance Ratings

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	500	$^{\circ}\text{C/W}$
Junction-to-Ambient – $t = 5$ s (Note 2)		447	

2. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	N	$V_{GS} = 0\text{ V}$	$I_D = 250\text{ }\mu\text{A}$	20		V
		P		$I_D = -250\text{ }\mu\text{A}$	-20		
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				18		mV/ $^{\circ}\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	N	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 25^{\circ}\text{C}$		1.0	μA
		P	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$			-1.0	
		N	$V_{GS} = 0\text{ V}, V_{DS} = 16\text{ V}$	$T_J = 125^{\circ}\text{C}$		2.0	μA
		P	$V_{GS} = 0\text{ V}, V_{DS} = -16\text{ V}$			-5.0	
Gate-to-Source Leakage Current	I_{GSS}	P	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 2.0	μA
		N				± 5.0	

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	N	$V_{GS} = V_{DS}$	$I_D = 250\text{ }\mu\text{A}$	0.45	1.0	V
		P		$I_D = -250\text{ }\mu\text{A}$	-0.45	-1.0	
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				-1.9		-mV/ $^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	N	$V_{GS} = 4.5\text{ V}, I_D = 540\text{ mA}$		0.4	0.55	Ω
		P	$V_{GS} = -4.5\text{ V}, I_D = -430\text{ mA}$		0.5	0.9	
		N	$V_{GS} = 2.5\text{ V}, I_D = 500\text{ mA}$		0.5	0.7	
		P	$V_{GS} = -2.5\text{ V}, I_D = -300\text{ mA}$		0.6	1.2	
		N	$V_{GS} = 1.8\text{ V}, I_D = 350\text{ mA}$		0.7	0.9	
		P	$V_{GS} = -1.8\text{ V}, I_D = -150\text{ mA}$		1.0	2.0	
Forward Transconductance	g_{FS}	N	$V_{DS} = 10\text{ V}, I_D = 540\text{ mA}$		1.0		S
		P	$V_{DS} = -10\text{ V}, I_D = -430\text{ mA}$		1.0		

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{ISS}	N	$f = 1\text{ MHz}, V_{GS} = 0\text{ V}$ $V_{DS} = 16\text{ V}$		80	150	pF
Output Capacitance	C_{OSS}				13	25	
Reverse Transfer Capacitance	C_{RSS}				10	20	
Input Capacitance	C_{ISS}	P	$f = 1\text{ MHz}, V_{GS} = 0\text{ V}$ $V_{DS} = -16\text{ V}$		105	175	
Output Capacitance	C_{OSS}				15	30	
Reverse Transfer Capacitance	C_{RSS}				10	20	

3. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	N/P	Test Condition	Min	Typ	Max	Unit
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CHARGES, CAPACITANCES AND GATE RESISTANCE

Total Gate Charge	$Q_{G(TOT)}$	N	$V_{GS} = 4.5\text{ V}, V_{DS} = -10\text{ V}; I_D = 540\text{ mA}$		1.5	2.5	nC
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	Q_{GS}				0.2		
Gate-to-Drain Charge	Q_{GD}				0.35		
Total Gate Charge	$Q_{G(TOT)}$	P	$V_{GS} = -4.5\text{ V}, V_{DS} = 10\text{ V}; I_D = -380\text{ mA}$		1.7	2.5	
Threshold Gate Charge	$Q_{G(TH)}$				0.1		
Gate-to-Source Charge	Q_{GS}				0.3		
Gate-to-Drain Charge	Q_{GD}				0.4		

SWITCHING CHARACTERISTICS ($V_{GS} = V$) (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	N	$V_{GS} = 4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = 540\text{ mA}, R_G = 10\ \Omega$		6.0		ns
Rise Time	t_r				4.0		
Turn-Off Delay Time	$t_{d(OFF)}$				16		
Fall Time	t_f				8.0		
Turn-On Delay Time	$t_{d(ON)}$	P	$V_{GS} = -4.5\text{ V}, V_{DD} = 10\text{ V}, I_D = -215\text{ mA}, R_G = 10\ \Omega$		10		
Rise Time	t_r				12		
Turn-Off Delay Time	$t_{d(OFF)}$				35		
Fall Time	t_f				19		

Drain-Source Diode Characteristics

Forward Diode Voltage	V_{SD}	N	$V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$	$I_S = 350\text{ mA}$		0.7	1.2	V
		P		$I_S = -350\text{ mA}$		-0.8	-1.2	
Reverse Recovery Time	t_{RR}	N	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}$	$I_S = 350\text{ mA}$		6.5		ns
		P		$I_S = -350\text{ mA}$		13		

4. Switching characteristics are independent of operating junction temperatures

N-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

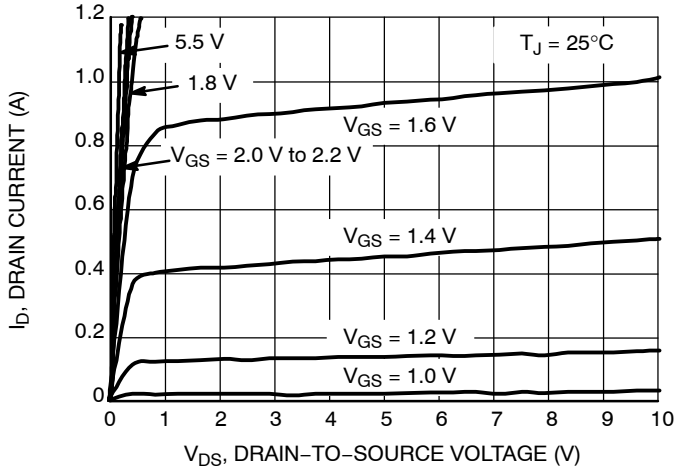


Figure 1. On-Region Characteristics

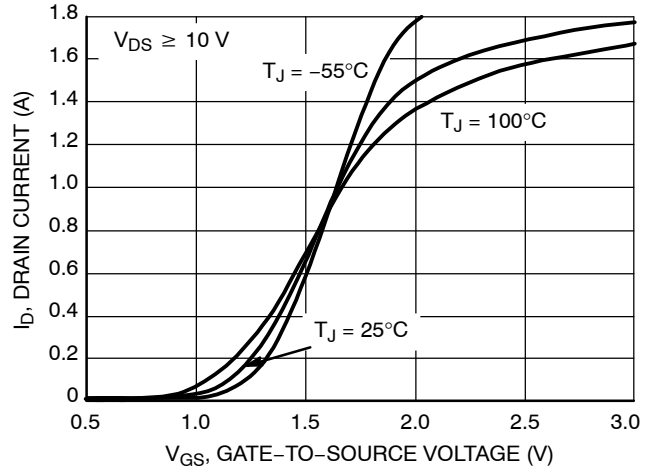


Figure 2. Transfer Characteristics

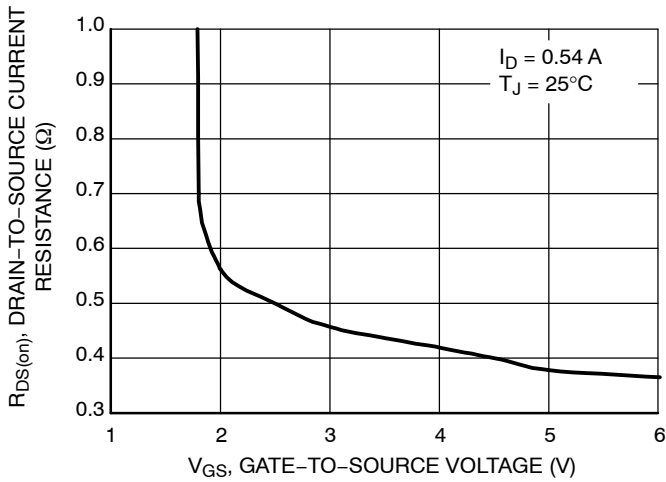


Figure 3. On-Resistance versus Gate-to-Source Voltage

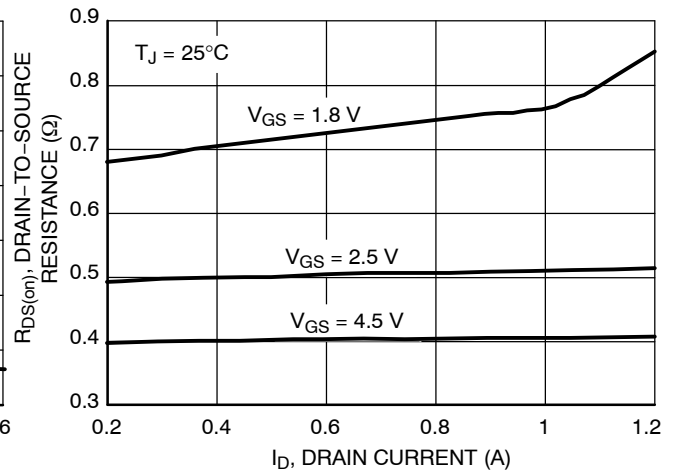


Figure 4. On-Resistance versus Drain Current and Gate Voltage

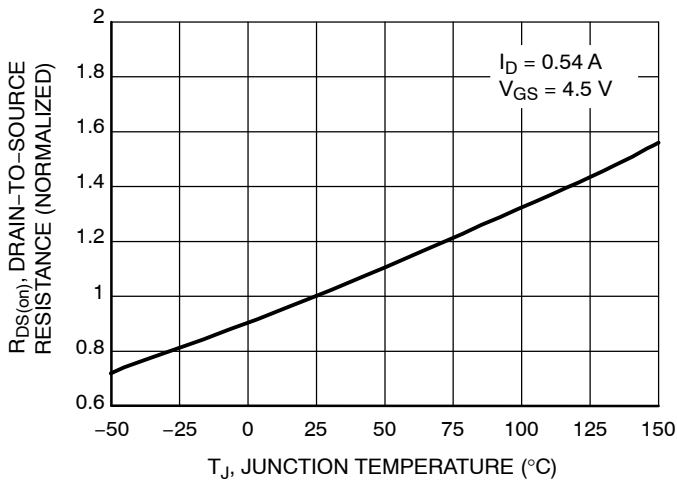


Figure 5. On-Resistance Variation with Temperature

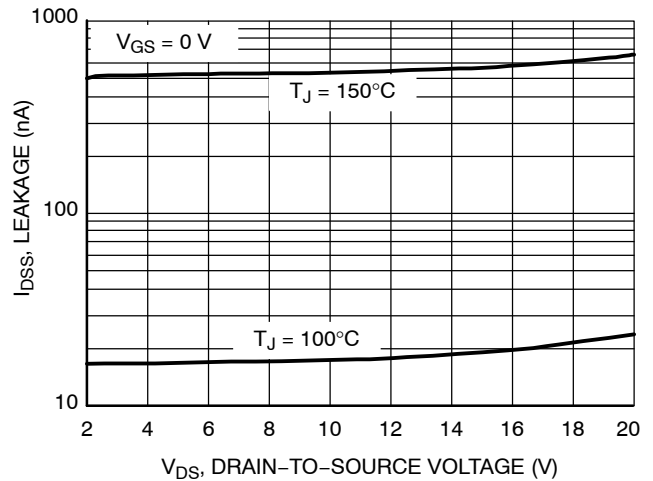


Figure 6. Drain-to-Source Leakage Current versus Voltage

N-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

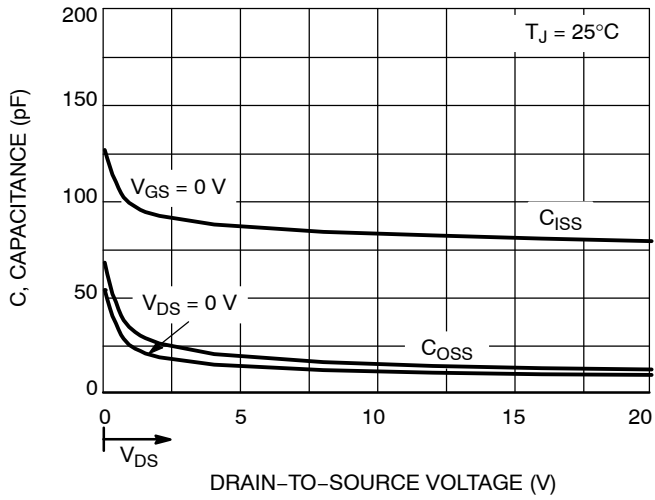


Figure 7. Capacitance Variation

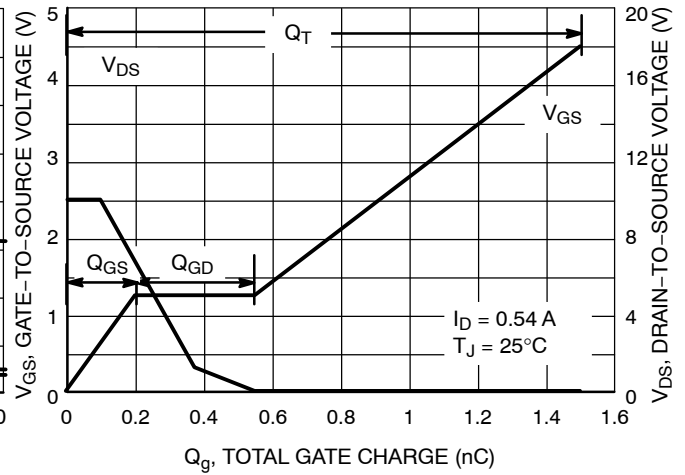


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

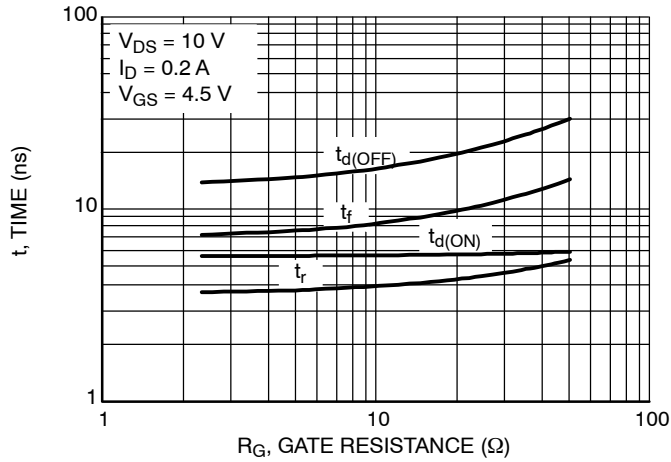


Figure 9. Resistive Switching Time Variation versus Gate Resistance

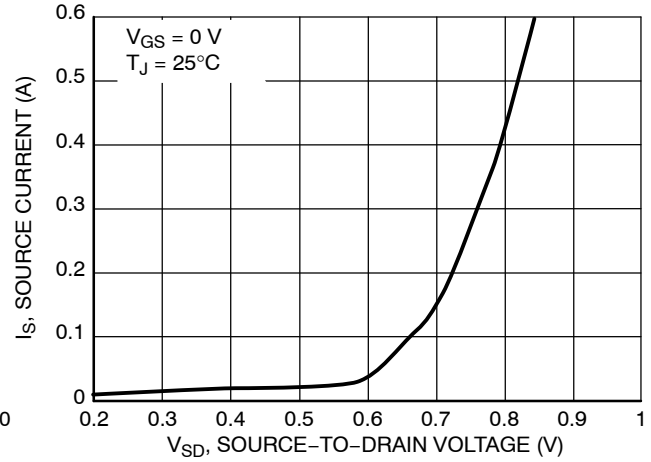


Figure 10. Diode Forward Voltage versus Current

P-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

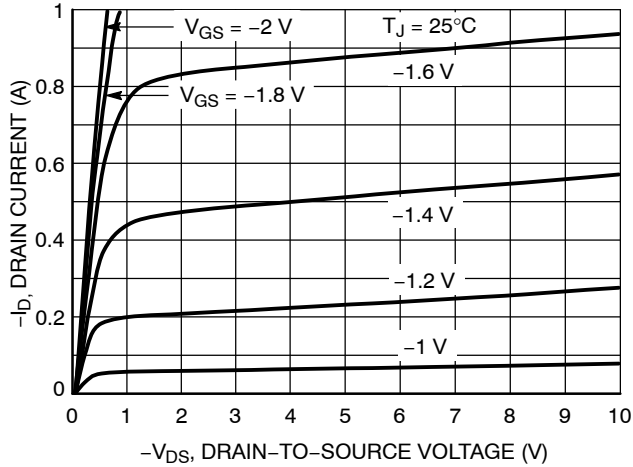


Figure 1. On-Region Characteristics

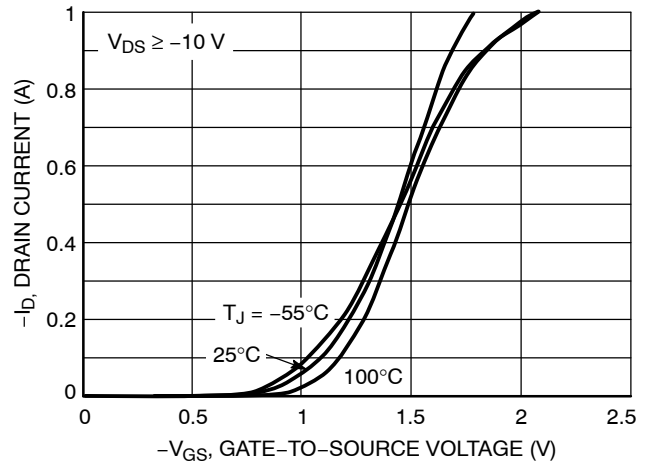


Figure 2. Transfer Characteristics

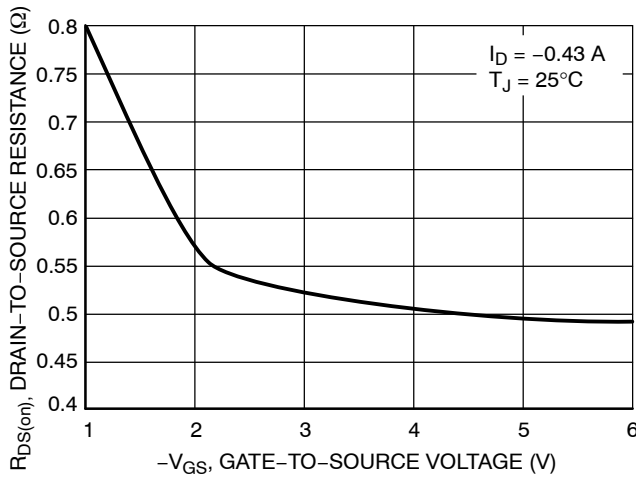


Figure 3. On-Resistance vs. Gate-to-Source Voltage

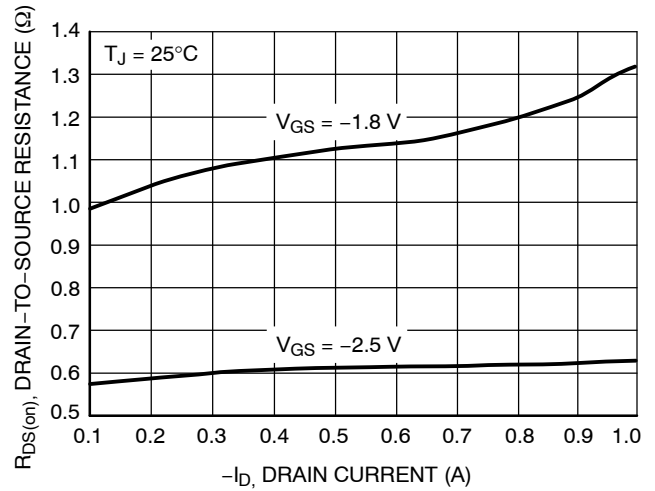


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

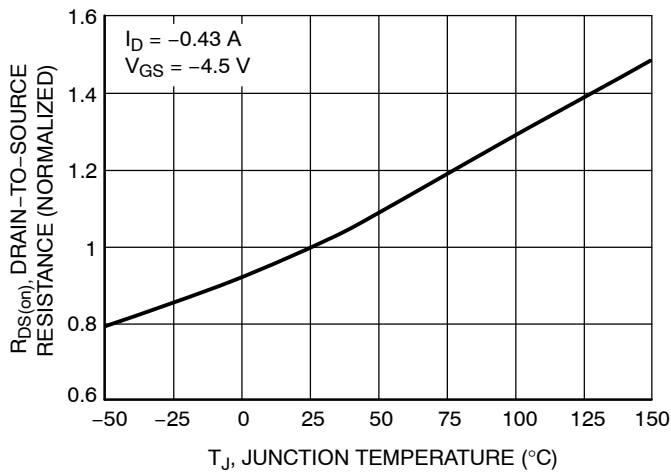


Figure 5. On-Resistance Variation with Temperature

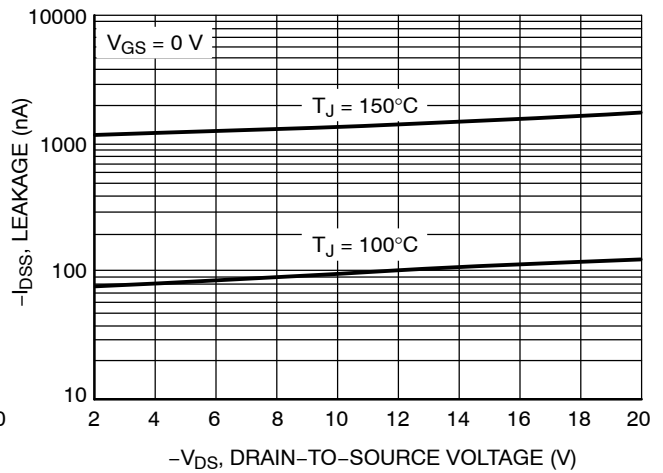


Figure 6. Drain-to-Source Leakage Current vs. Voltage

P-CHANNEL TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

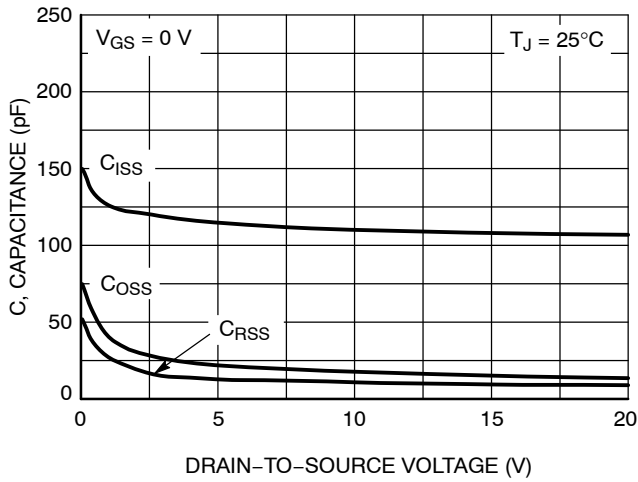


Figure 7. Capacitance Variation

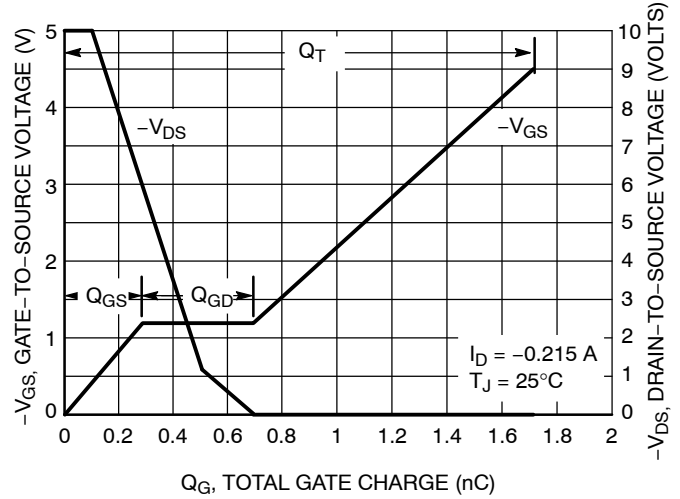


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

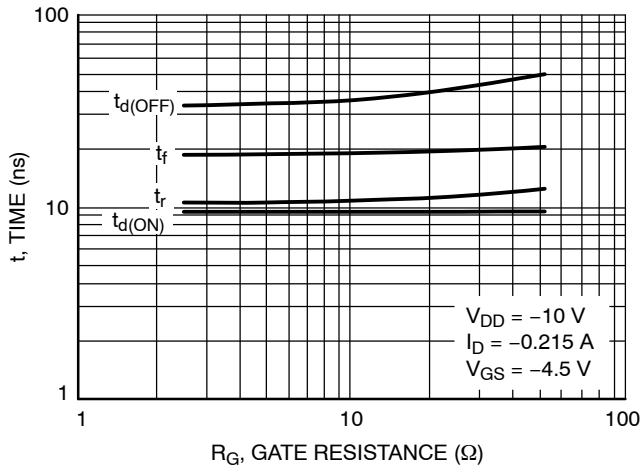


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

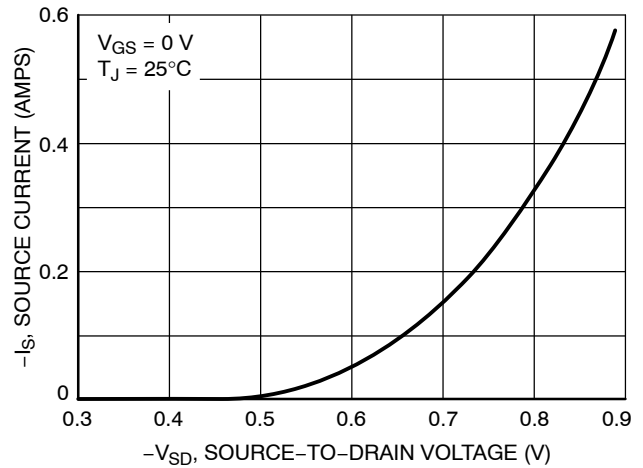


Figure 10. Diode Forward Voltage vs. Current



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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